Low-Dimensional and Extended Metal—Metal Bonded Networks in Transition Metal Compounds: Ba₂Nb₅O₉, Ba_{2-x}Y_xNb₅O₉

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The crystal structure, oxidation state, electronic properties of unusual niobates which contain niobium clusters condensed low dimensionally, were investigated by X-ray diffraction, X-ray photoelectron spectroscopy (XPS), electrical resistivity measurements, and Raman spectroscopy. The results of XPS experiment indicate that there are three niobium oxidation states (Nb⁴⁺, Nb³⁺, Nb²⁺) in Ba₂Nb₅O₉ and these oxidation states are expected to be stable considering their atomic coordinates. Pure BaNbO₃ phase was synthesized and its niobium oxidation state was examined in order to compare with those of niobium in Ba₂Nb₅O₉. Electrical resistivity measurements on Ba₂Nb₅O₉ show negative $d\rho/dT$ behavior between 160 K and 600 K. Similar behavior was observed in yttrium substituted niobates, Ba_{2-x}Y_xNb₅O₉. The possibility of relationship between low dimensionality and anomalous properties of these niobates is discussed. © 1994 Academic Press, Inc.

1. INTRODUCTION

Since Svensson and co-workers found Ba₂Nb₅O₉, there have been growing interests in similar new reduced niobates (1-3). Michelson et al. have found more niobate phases (Sr₂Nb₅O₉, K₂Nb₅O₉, and KNb₃O₅) and reported anomalous electronic properties in Ba₂Nb₅O₉ (4). These niobates commonly contain Nb₆O₁₂ and NbO₆ octahedral clusters and their structures can be described as an intergrowth of perovskite-like Ba₂NbO₄ and NbO-like Nb₄O₅ layers. Three-dimensional condensation of Nb₆O₁₂ octahedral clusters (the octahedral Nb6 clusters are edgecapped by twelve oxygens to make Nb₆O₁₂ clusters, and Nb₆ clusters are condensed by sharing corners) occurs in NbO and that of NbO₆ clusters (by sharing corners) occurs in BaNbO₃. In Ba₂Nb₅O₉, three-dimensional networks of Nb₆O₁₂ and NbO₆ octahedral clusters are modified to become two-dimensional layers, and these two layers are intergrown in ordered way as shown in Fig. 5.

Even though the cubic BaNbO₃ phase was first reported in 1955 (5), the exact barium occupancy is not clearly

known. Kreiser and Ward reported barium deficient perovskite (6) and recently Svensson reported perovskite with full barium occupancy (7). However, it was known that strontium occupancy ranges from 0.7 to 0.95, and unit cell parameters obey the Vegard law in Sr, NbO₃ perovskite. We synthesized a pure BaNbO, phase and compared the niobium character of this material with that of Ba₂Nb₅O₉. Results of our X-ray photoelectron spectroscopic (XPS) experiments show that Ba₂Nb₅O₉ has three kinds of Nb atoms in different oxidation states, while all Nb atoms of BaNbO₃ are in one oxidation state (Nb $^{4+}$). We examined electrical resistivity of Ba₂Nb₅O₉ and $Ba_{2-x}Y_xNb_5O_9$, and found negative $d\rho/dT$ behavior between 160 and 600 K. The origin of these anomalous electronic properties is conjectured to be diffusion of charge carriers between layers (8).

2. EXPERIMENTAL

Two reduced niobates, $Ba_2Nb_5O_9$ and $BaNbO_3$, were synthesized from fully oxidized niobium compound, $Ba_5Nb_4O_{15}$. To synthesize $Ba_2Nb_5O_9$ and $BaNbO_3$, stoichiometric amounts of Nb, Nb_2O_5 , and $Ba_5Nb_4O_{15}$ were ground and pressed into pellets, then heated to $1050^{\circ}C$ for 24 hr in an evacuated quartz tube. $Ba_5Nb_4O_{15}$ was prepared from mixture of $BaCO_3$ and Nb_2O_5 , and heated to $1100^{\circ}C$ in air for 24 hr. $Ba_{2-x}Y_xNb_5O_9$ was synthesized from Y_2O_3 , Nb, Nb_2O_5 , and $Ba_5Nb_4O_{15}$ in a way similar to $Ba_2Nb_5O_9$.

X-ray measurements were taken at room temperature using a Siemens X-ray diffractometer and $CuK\alpha$ radiation. Diffraction data were analyzed using Rietveld-type full-profile refinement technique (9), using a measuring step of 0.02° (in 2 θ). A Rigaku X-ray diffractometer equipped with a Bühler sample chamber and temperature controller was used for studies at high temperatures (up to 900°C).

Electrical resistivities were measured using the fourprobe method and sintered pellets. For low temperature (liquid nitrogen range) experiments, four wires were connected to the sample by indium contacts. For higher tem-

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perature experiments (from room temperature to 900 K), tungsten wires were pressed to the sample directly and measurements were carried out under an argon atmosphere.

XPS experiments were carred out with a Surface Science instrument. Samples were mounted on an aluminum plate. Nonmonochromatic Al $K\alpha$ radiation was used as an excitation source ($h\nu=1486.6~{\rm eV}$). During the measurement, the spectrometer was pumped to a residual pressure of about 10^{-9} Torr. The sample surfaces were mechanically scraped with a metal brush or sputtered by ion bombardment in order to expose fresh surfaces the 1s binding energy of carbon, 284.6 eV, was used as an internal standard.

Raman spectroscopy experiments were carried out with a Jobin Yvon U1000 double monochromator and the 514.5 nm line of Ar-ion laser in a back scattering geometry. Slit widths were 500 μ m, corresponding to 4.6 cm⁻¹ resolution. To obtain reproducible data, several crystals from the same pellet were measured during the experiments.

Tight-binding electronic structure calculation based upon the extended Hückel method (10) was performed for the Ba₂Nb₅O₉ system.

3. RESULTS AND DISCUSSION

The product with stoichiometry of Ba₂Nb₅O₉ was a homogeneous black powder. The powder X-ray diffraction pattern was refined with Rietveld-type full profile refinement. No extra peaks except the calculated pattern were found. The refined parameters used were scale factor, zero point, background parameters, cell parameters, atomic positions, and occupancies. No partial occupancies were indicated within standard deviations. (Fig. 1, Table 1)

The product with stoichiometry of BaNbO₃ was bright violet with metallic luster. The X-ray diffraction pattern did not have any impurity lines. Since we were interested in the oxidation state of Nb, we examined the occupancy of Ba sites using the Rietveld method and found the barium sites were fully occupied within standard deviation (fitting results are shown in Fig. 2). If the actual composition of this material were Ba_{0.5}NbO₃, the oxidation state of Nb could be +5. Direct current magnetic susceptibility measurement showed Pauli paramagnetism (7.2 \times 10⁻⁷ emu/g), with absolute error of 20% at room temperature. A typical metallic behavior was observed with the resistivity of 2.8×10^{-3} ohm cm at 298 K. The maximum oxidation state of Nb is +5 with d° electron configuration, and fully oxidized niobates are insulators. However, the results of resistivity and susceptibility measurements confirm that this material is metallic. XPS experiments were carried out (Fig. 3) on a mechanically-scraped surface and the results are listed in Table 2. The experiments were

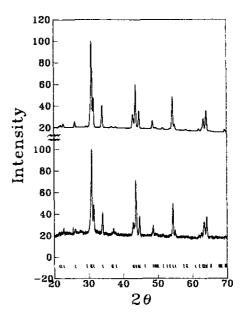


FIG. 1. Comparison of calculated (top) and observed (bottom) powder diffraction for Ba₂Nb₅O₉. Vertical strokes indicate calculated Bragg peak positions.

performed also on an argon-sputtered surface. Two different methods to get clean surfaces were tried as above and the results were the same in this compound. The binding energy of Nb showed good agreement with NIST data for NbO₂ (11). The resistivity, susceptibility measurement, and XPS experiments suggest that the oxidation state of niobium in BaNbO₃ is +4 and d^1 electrons are delocalized.

To examine the oxidation state of niobium in various chemical bondings, XPS experiments were carried out (Fig. 4) for Ba₂Nb₅O₉. The surfaces of sample were prepared by the two methods as in BaNbO₃. Comparing two sets of data after the two different surface treatments, the data after argon sputtering showed multiple peaks

TABLE 1
Refined Parameters for Ba₂Nb₅O₉ in Tetragonal
P4/mmm Unit Cell

Atom	Position (x, y, z)	Occupancy (%)		
Ba	0, 0, 0.333(9)	100 (1)		
Nb1	$\frac{1}{2}, \frac{1}{2}, \frac{1}{2}$	100 (1)		
Nb2	$\frac{1}{2}$, $\frac{1}{2}$, 0.1677(9)	100 (1)		
Nb3	$0, \frac{1}{2}, 0$	100 (1)		
01	$\frac{1}{2}$, 0, $\frac{1}{2}$	not refined		
02	$\frac{1}{2}$, $\frac{1}{2}$, 0.347(3)	not refined		
03	$\frac{1}{2}$, 0, 0.2032(9)	not refined		
04	0, 0, 0	not refined		

Note. The figures within parentheses are the estimated standard deviations based on statistics. Refined results: $R_{\rm wp} = 6.61\%$. Unit cell: a = 4.1659(2) Å, c = 12.2256(9) Å.

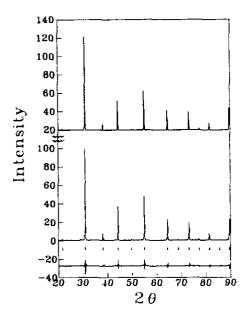


FIG. 2. Comparison of calculated (top) and observed (bottom) powder diffraction for $BaNbO_3$. Vertical strokes indicate calculated Bragg peak positions. No extra peaks are indicated. The unit cell parameter refined is 4.0939(3) Å in Pm3m. The resulting weighted profile R-value is 13%.

resolved clearly. XPS results from sputtered surfaces, especially surfaces of oxides, could have artifacts of reduction instead of a surface-cleaning effect. Since the change in oxidation state of niobium after ion sputtering was not observed in BaNbO₃, we may assume that the reduction is not serious for a qualitative analysis on similar

TABLE 2 Niobium $3d_{3/2}$. $3d_{5/2}$ Binding Energy of the BaNbO₃

Binding energy (eV)	State	Intensity (%)
209.1 ± 0.2	d _{3/2} (Nb ⁺⁴)	42
206.3 ± 0.2	$d_{5/2} (\mathrm{Nb}^{+4})$	58

niobate, $Ba_2Nb_5O_9$. The XPS results for niobium $3d_{3/2}$ and $3d_{5/2}$ binding energies are listed in Table 3. Peaks could be resolved into 3 pairs of $d_{3/2}$ and $d_{5/2}$. Crystallographically, there are two kinds of niobium, Nb(2) and Nb(3), in the Nb₄O₅ layers. Since Nb(1) has same NbO₆ coordination as in BaNbO₃ (Fig. 5), the oxidation state of Nb(1) could be assigned to +4, which corresponds to the peak at the highest binding energy in Fig. 4. The two peaks at lower binding energies could be assigned to Nb³⁺ for Nb(2) and Nb2+ for Nb(3), and these assignments seem to be reasonably based not only on charge balance but also on atomic coordinates around niobium atoms. Three different oxidation states are expected to be stable based on following reasons. There are six oxygens coordinated to Nb(1), the bond lengths of Nb(1)-O(1) and Nb(1)-O(2) are 2.08 and 1.54 Å, respectively (Fig. 6). Employing a crystal field approach, the energy levels of d orbitals are expected to be split into sublevels to stabilize the $d_{x^2-y^2}$, d_{rv} orbitals in a tetrahedrally contracted octahedral field and d^1 configuration is reasonably stable in Nb(1). There are five oxygen atoms coordinated around Nb(2). The bond lengths of four Nb(2)-O(3) and one Nb(2)-O(2) are 2.10 and 2.48 Å, respectively. The energy levels of d_{xz} ,

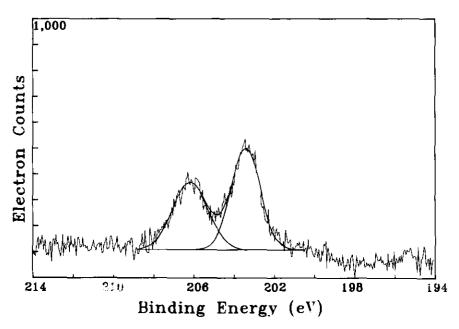


FIG. 3. Nb 3d core-level XPS spectrum for the BaNbO₃.

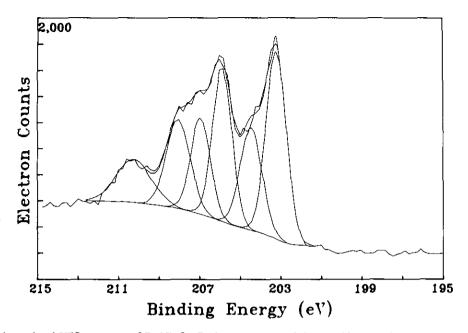


FIG. 4. Nb 3d core-level XPS spectrum of Ba₂Nb₅O₉. Peaks are sextet and they could be resolved into three pairs of doublets.

Table 3
Niobium $3d_{3/2}$, $3d_{5/2}$ Binding Energy of the Ba₂Nb₅O₉ after Argon Ion Sputtering

Binding energy (eV)	State	Intensity (%)
209.2 ± 0.2	d _{3/2} (Nb ⁺⁴)	10
207.0 ± 0.2	$d_{5/2} (\text{Nb}^{+4})$	14
206.0 ± 0.2	$d_{3/2} (\text{Nb}^{+3})$	10
203.6 ± 0.2	$d_{5/2} (\mathrm{Nb}^{+3})$	16
205.0 ± 0.2	$d_{3/2} (Nb^{+2})$	20
202.2 ± 0.2	$d_{5/2}$ (Nb ⁺²)	27

 d_{yz} , d_z^2 orbitals are expected to be lowered, and in this circumstance d^2 configuration is stable. There are four oxygen atoms coordinated around Nb(3) and the bond lengths of the two Nb(3)-O(3) and two Nb(3)-O(4) are 2.34 and 2.08 Å, respectively. In this square planar field, the energy levels of d_z^2 , d_{xz} , d_{yz} orbitals are expected to be lowered and d^3 configuration is stable.

In $Ba_2Nb_5O_9$, a maximum value of resistivity at 160 K has been observed as reported previously (4). The room temperature resistivity was 6.0×10^{-3} ohm cm with absolute error of 20% and most of the error is due to the uncertainty in the geometry of the electric contacts. We

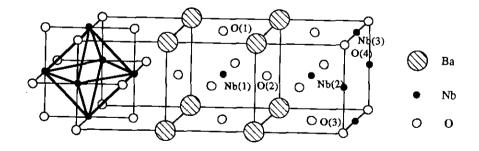




FIG. 5. The structure of Ba₂Nb₅O₉. This structure can be described as an alternating building block of perovskite-type NbO₆ layer and Nb₆ octahedra (heavily outlined) layer.

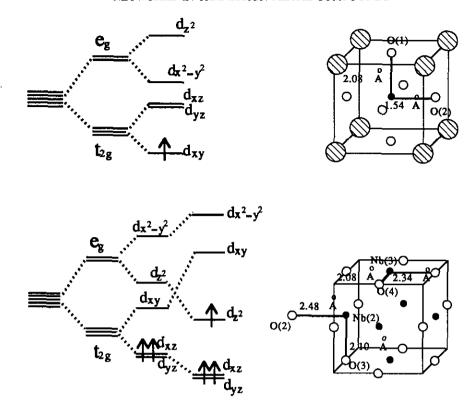


FIG. 6. Splittings of d-orbital energies of (a) in a tetragonally contracted octahedral field (b) tetrahedrally elongated octahedral field and square planar field.

measured the resistivities up to 750 K and found a change in sign of $d\rho/dT$ approximately at 600 K. The $d\rho/dT$ is negative between 160 K and 600 K (Fig. 7). This feature could possibly be driven by a charge density wave (CDW).

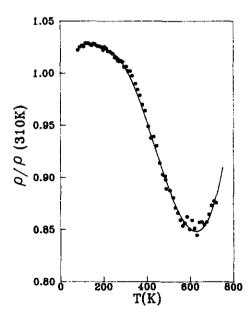


FIG. 7. Normalized resistivity vs. temperature for $Ba_2Nb_5O_9$. A maximum value of resistivity at ~ 160 K, a change in sign of temperature dependency at ~ 600 K has been observed.

Similar phenomena are observed for a quasi-one dimensional metallic system such as molybdenium oxide bronze and quasi-low dimensional compounds (12–15). However, no nonohmic behavior was observed for $Ba_2Nb_5O_9$ up to 530 mV/cm in field strength. To examine how the electronic structure is related to physical properties in $Ba_2Nb_5O_9$, we have calculated the electronic band structures of the $Nb_5O_9^{4-}$ unit in $Ba_2Nb_5O_9$ using the parameter in Table 4. The results show the presence of three partially filled d block bands, which indicates the presence of a two-dimensional Fermi surface (Fig. 8). No phase transition at 600 K was confirmed by X-ray diffraction. High-temperature X-ray diffraction (up to 1200 K) patterns did not

TABLE 4
Parameters for EH calculation in Ba₂Nb₅O₉

Atom	Orbital	H_{ii} (eV) ^a	$\xi_1(c_1)$	$\xi_2^b(c_2)^c$
Nb	5 <i>s</i>	- 10.10	1.89	
	5p	-6.86	1.85	
	4 <i>d</i>	-12.10	4.08(0.6401)	1.64(0.5516)
0	2 <i>s</i>	-14.8	2.275	
	2 <i>p</i>	-33.3	2.275	

^a H_{ii} , valence orbital ionization potential.

^b ξ, Slater-type orbital exponents.

^c c, coefficients used in double- ξ expansion of orbitals.

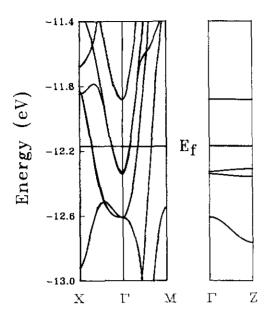


FIG. 8. Low-lying d-block bands calculated for the Nb_5O_9 unit in $Ba_2Nb_5O_9$. The results show the presence of three partially filled d-block band which indicates open Fermi surface along ab layer direction.

have any difference from those at room temperature. This result suggests that the change in sign of $d\rho/dT$ at 160 and 600 K is not due to structural phase transition or any thermal disintegration.

To further examine the anomalous electronic behavior, $Ba_{2-x}Y_xNb_5O_9$ (x=0.05,0.10,0.20) were prepared. When x increased, the cell parameters decreased as shown in Fig. 9. The Raman spectra of these compounds confirm that the yttrium dopants substituted Ba sites. As shown in Table 5 six peaks in total were observed in various compositions of $Ba_{2-x}Y_xNb_5O_9$. Because the space group of this compound is P4/mmm, A_{1g} , B_{1g} , and E_g modes are expected to be observed. Figure 10 shows the modes

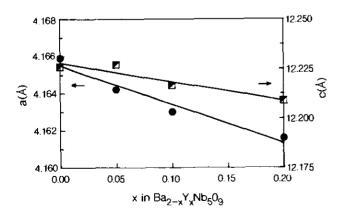


FIG. 9. Change in the lattice parameters a and c as a function of Y content in $Ba_{2-x}U_xNb_5O_9$.

TABLE 5 Frequencies in cm $^{-1}$ of Raman vibrational modes in $Ba_{2-x}Y_xNb_5O_9$

) 				
Composition (x)	$ \overline{\nu_1} $	ν_2	ν_3	$\overline{\nu_4}$	ν ₅	ν_6
0	131	162	237	503	 539	634
0.05	135	162	236	503	536	629
0.1	136	161	237	503	538	633
0.2	139	163	237	502	537	630

at low frequencies along with an Ar-plasma line at 117 cm⁻¹. Among 6 peaks, only the peak with lowest frequency, 131 cm⁻¹, shifted to higher frequency when the yttrium content increased. The increase of the frequency of Ba A_{1g} mode suggests that the lighter yttrium atoms substituted for Ba atoms.

For Ba_{2-x}Y_xNb₅O₉ samples as well, negative $d\rho/dT$ behavior was observed, but the maxima of resistivity were observed at a higher temperature than in the undoped sample. Resistivity curves normalized to 1 at 297 K are shown in Fig. 11 along with that of undoped sample. All yttrium-doped samples show negative $d\rho/dt$ behavior above 230 K, which is at a higher temperature than in the undoped sample. The positive $d\rho/dT$ behavior is usually regarded as metallic and the negative $d\rho/dT$ behavior as semiconducting. However, even if it is not metallic the positive $d\rho/dT$ behavior is also possible from the tempera-

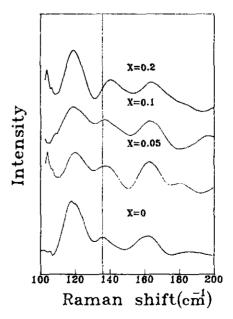


FIG. 10. Raman spectra of $Y_xBa_{2-x}Nb_5O_9$ (x = 0.00, 0.05, 0.10, 0.20). The peak near 117 cm⁻¹ is a Ar-plasma line. Note the shift of 131 cm⁻¹ mode with Y substitution on Ba site.

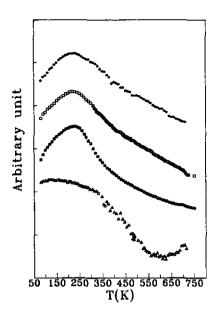


FIG. 11. Normalized resistivity vs temperature for $Y_xBa_{2-x}Nb_5O_9$ (x = 0.00, 0.05, 0.10, 0.20 from bottom to top). Resistivity is plotted on a linear scale

ture dependence of the in-plane lifetime of the carriers which tunnel to the neighboring planes in two-dimensional metals (16). In such a case, the $d\rho/dT < 0$ behavior may come from phonon-assisted hopping when disorder is introduced between the planes (8). However, our samples are polycrystalline. Thus, the resistivity curves represent a mixture of in-plane and interplane resistivities. For the undoped sample (x = 0), in-plane resistivity seems to be small, thereby leading to a smooth temperature-dependence of resistivity. As the samples are doped by vttrium, the disorder effect seems to increase the in-plane resistivity. This would make the total resistivity more strongly determined by the interplane resistivity, which has a $d\rho/dT < 0$ behavior at high temperature due to phononassisted hoping as disorder sets in. The three curves (x = 0.05, 0.10, 0.20) show a maximum at almost identical temperatures. It is possible that the substitution of Y is saturated by the amount of x = 0.05.

Michelson et al. reported electrical resistivity of single phase BaSrNb₅O₉ with lattice constants a=4.150 Å, c=12.021 Å (4). In the measured temperature range below 325 K, the resistivity does not show any maximum as does Ba_{2-x}Y_xNb₅O₉. In BaSrNb₅O₉, which has much smaller lattice parameters than Ba_{2-x}Y_xNb₅O₉, the in-plane lifetime of the carriers would be much shorter than in Ba_{2-x}Y_xNb₅O₉ due to more active hopping. Therefore the

total resistivity, which is determined by the competition between the in-plane lifetime term and the phonon-assisted term, is expected to show its maximum at much higher temperatures than 230 K, possibly higher than 325 K. Obviously, it is not ruled out that the $d\rho/dT < 0$ behavior could come from the semiconducting nature or even from the decrease of the c-axis band gap with increasing temperature.

In summary, we prepared two reduced niobates, $BaNbO_3$ and $Ba_{2-x}Y_xNb_5O_9$. Raman results in $Ba_{2-x}Y_xNb_5O_9$ confirm that Y atoms substitute in Ba sites. XPS experiments indicate that there are three different oxidation states of niobium in $Ba_2Nb_5O_9$ and one oxidation state of Nb^{4+} in $BaNbO_3$. Based on electrical resistivity measurements, we suggest that the negative resistivity versus temperature dependence originates from phononassisted hopping between planes as disorder is introduced.

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